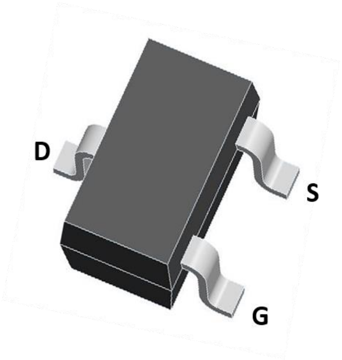
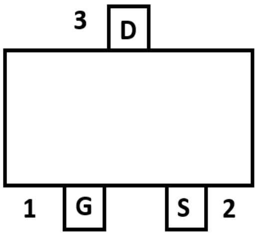
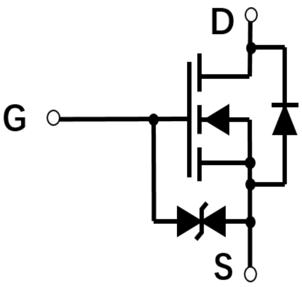
N-Channel Enhancement Mode Field Effect Transistor





SOT-323



Product Summary

● V_{DS}	30V
● I_D	300mA
● $R_{DS(ON)}$(at V_{GS}=10V)	＜8.0ohm
● $R_{DS(ON)}$(at V_{GS}=4.5V)	＜13.0ohm

- ESD Protected Up to 2.5KV (HBM)

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface：TTL/CMOS

■ Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	30	V
Gate-source Voltage	V_{GS}	±20	V
Drain Current	I_D	300	mA
Pulsed Drain Current [A]	I_{DM}	1.5	A
Total Power Dissipation @ T_A=25℃	P_D	350	mW
Thermal Resistance Junction-to-Ambient @ Steady State [B]	$R_{\theta JA}$	357	℃/ W
Junction and Storage Temperature Range	T_J ,T_{STG}	-55～+150	℃

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V			1	μA
Gate-Body Leakage Current	I_{GSS1}	V_{GS}= ±20V, V_{DS}=0V			±10	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	0.65		1.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}= 10V, I_D=300mA		2.5	8.0	Ω
		V_{GS}= 4.5V, I_D=200mA		3.0	13.0	
Diode Forward Voltage	V_{SD}	I_S=300mA,V_{GS}=0V			1.2	V
Maximum Body-Diode Continuous Current	I_S				340	mA
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=30V,V_{GS}=0V,f=1MHZ		18		pF
Output Capacitance	C_{oss}			12		
Reverse Transfer Capacitance	C_{rss}			7		
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V,V_{DS}=30V,I_D=0.3A		1.7	2.4	nC
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V,V_{DD}=30V, I_D=300mA, R_{GEN}=6Ω		5		ns
Turn-off Delay Time	$t_{D(off)}$			17		
Reverse recovery Time	t_{rr}	V_{GS}=0V,I_S=300mA,V_R=25V, dI_S/dt=-100A/μs		30		ns

A. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.
B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

■ Typical Performance Characteristics

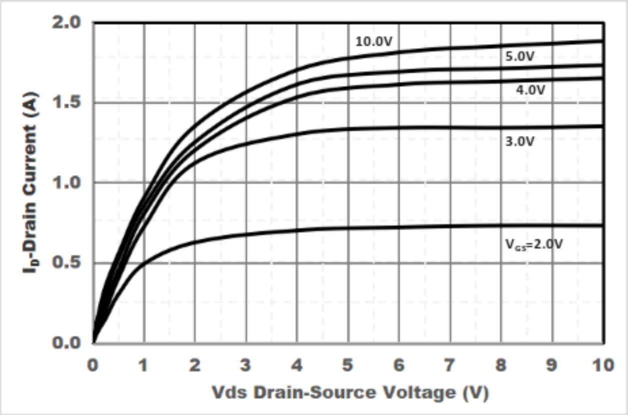


Figure1. Output Characteristics

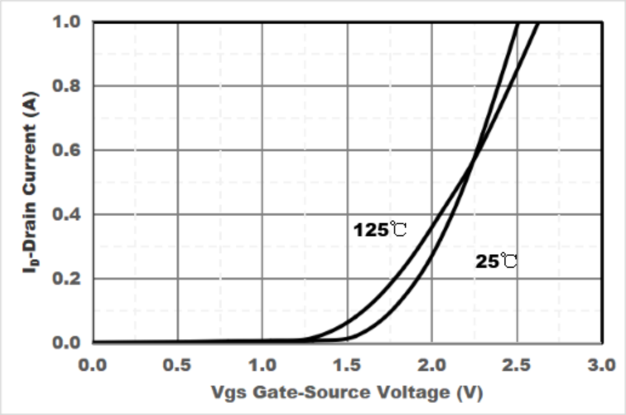


Figure2. Transfer Characteristics

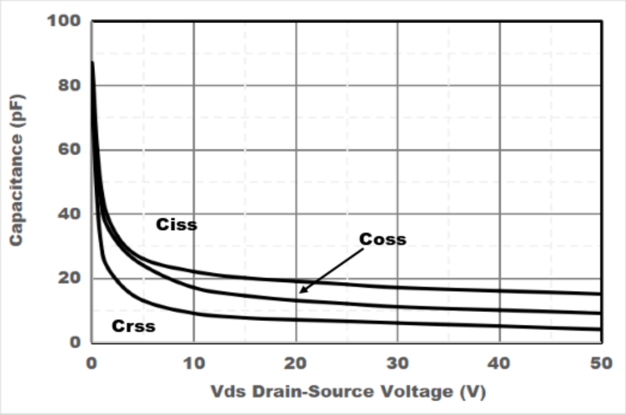


Figure3. Capacitance Characteristics

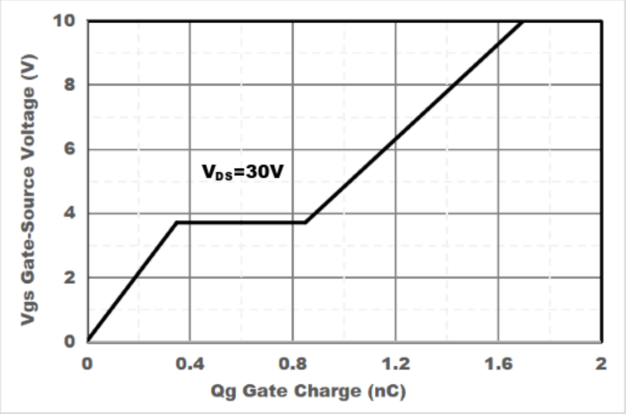


Figure4. Gate Charge

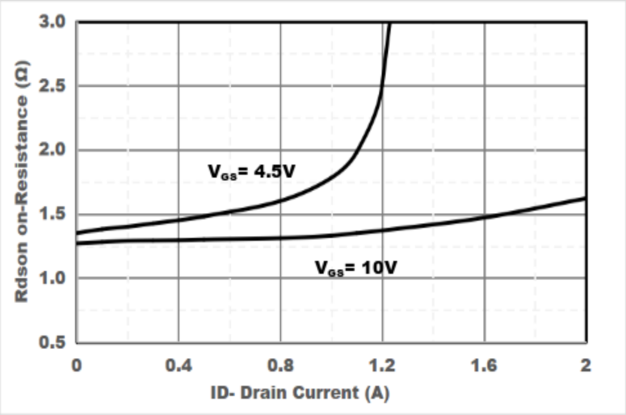


Figure5. Drain-Source on Resistance

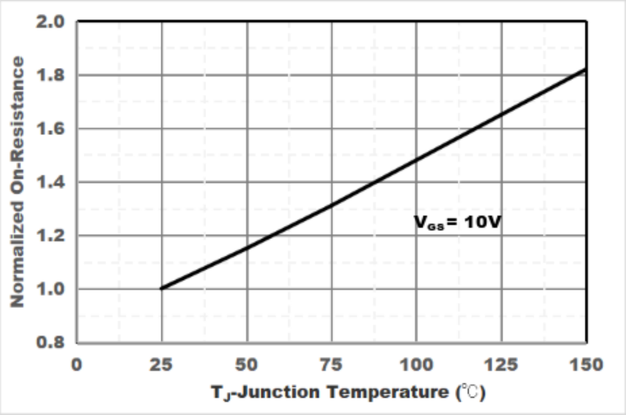


Figure6. Drain-Source on Resistance

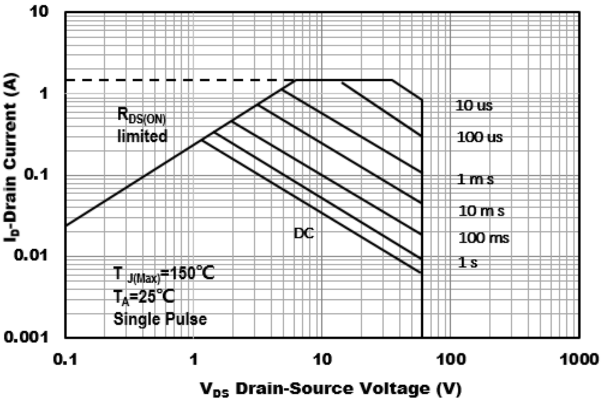


Figure7. Safe Operation Area

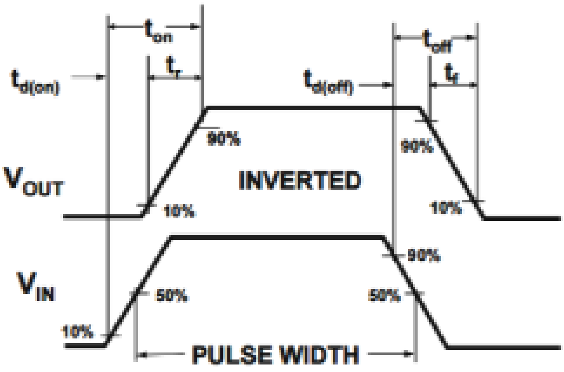
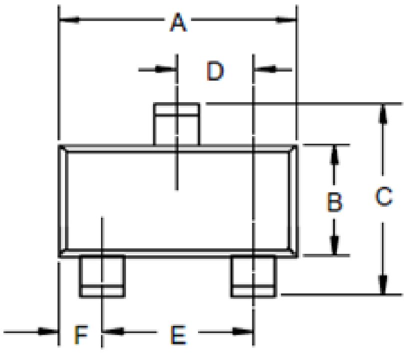
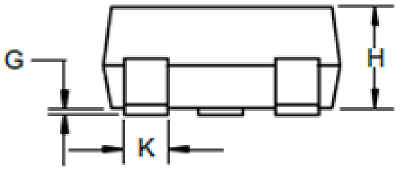


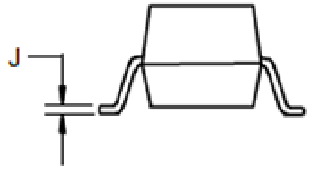
Figure8. Switching wave

■ SOT-323 Package information



DIM	INCHES MIN	INCHES MAX	MM MIN	MM MAX	NOTE
A	.071	.087	1.80	2.20	
B	.045	.053	1.15	1.35	
C	.083	.096	2.10	2.45	
D	.026 Nominal		0.65Nominal		
E	.047	.055	1.20	1.40	
F	.012	.016	.30	.40	
G	.000	.004	.000	.100	
H	.035	.039	.90	1.00	
J	.004	.010	.100	.250	
K	.006	.016	.15	.40	





■SOT-323 Suggested Pad Layout